



PJW4N10

100V N-Channel Enhancement Mode MOSFET

Voltage **100 V** **Current** **4 A**

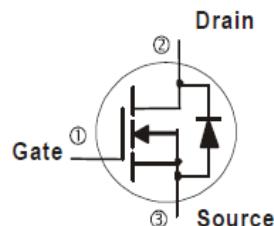
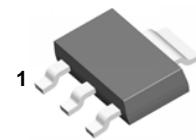
Features

- $R_{DS(ON)}$, $V_{GS}@10V, I_D@2A < 258m\Omega$
- $R_{DS(ON)}$, $V_{GS}@6V, I_D@1A < 268m\Omega$
- Low On-Resistance
- Low input capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.
(Halogen Free)

Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W4N10

SOT-223



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $T_C=25^\circ C$	I_D	4	A
$T_C=100^\circ C$	I_D	2.5	
Pulsed Drain Current ^(Note 1)	I_{DM}	8	
Power Dissipation $T_C=25^\circ C$	P_D	8	W
$T_C=100^\circ C$	P_D	3.2	
Continuous Drain Current $T_A=25^\circ C$	I_D	2.5	A
$T_A=70^\circ C$	I_D	2	
Power Dissipation	P_D	3.1	W
Power Dissipation	P_D	2	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	°C
Typical Thermal resistance ^(Note 4,5)	Junction to Case	$R_{\theta JC}$	15.6
	Junction to Ambient	$R_{\theta JA}$	40.3

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	2.85	3.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2A$	-	210	258	$m\Omega$
		$V_{GS}=6V, I_D=1A$	-	220	268	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic <small>(Note 6)</small>						
Total Gate Charge	Q_g	$V_{DS}=60V, I_D=4A,$ $V_{GS}=10V$ <small>(Note 2,3)</small>	-	6.7	-	nC
Gate-Source Charge	Q_{gs}		-	2.1	-	
Gate-Drain Charge	Q_{gd}		-	1.1	-	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	378	-	pF
Output Capacitance	C_{oss}		-	26	-	
Reverse Transfer Capacitance	C_{rss}		-	20	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=50V, RL=12.5\Omega,$ $V_{GS}=10V, R_G=6\Omega$ <small>(Note 2,3)</small>	-	4.3	-	ns
Turn-On Rise Time	t_r		-	22	-	
Turn-Off Delay Time	$t_{d(off)}$		-	9.7	-	
Turn-Off Fall Time	t_f		-	8.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	4	A
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$	-	0.78	1.2	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_J(MAX)=150^\circ C$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ C$.
4. The maximum current rating is package limited
5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing



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TYPICAL CHARACTERISTIC CURVES

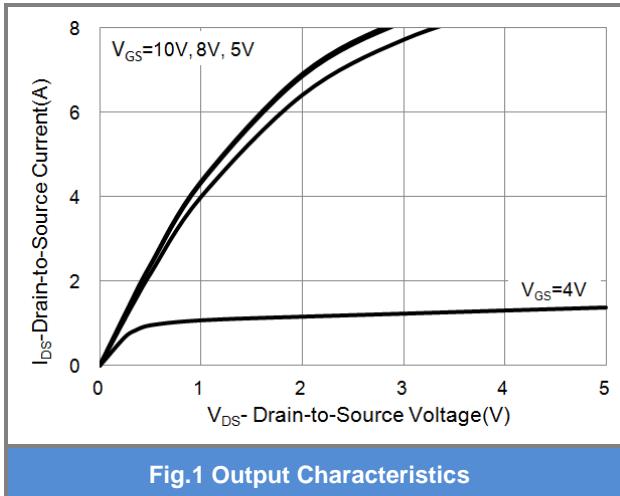


Fig.1 Output Characteristics

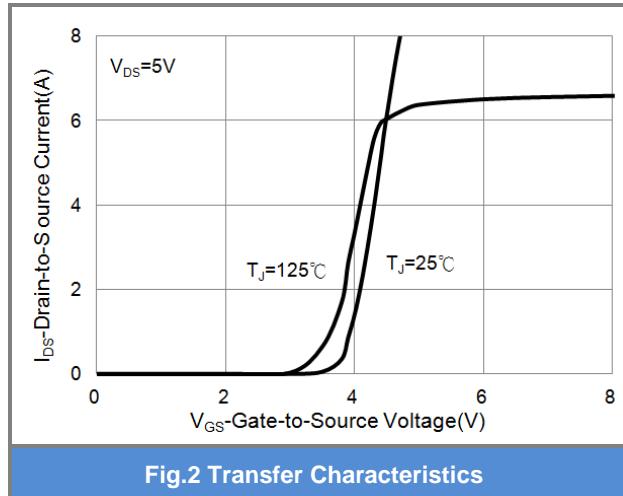


Fig.2 Transfer Characteristics

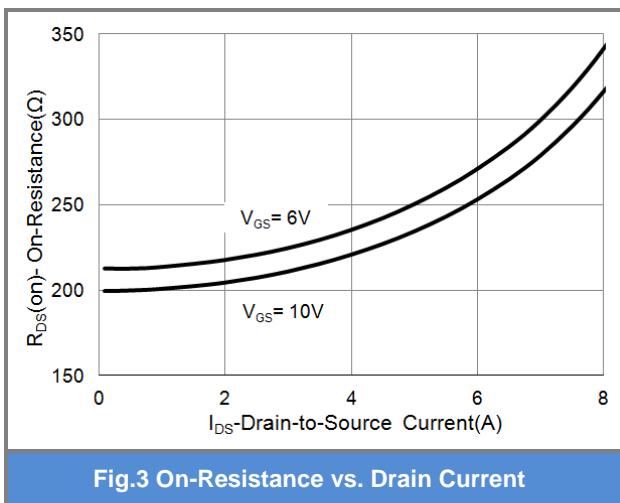


Fig.3 On-Resistance vs. Drain Current

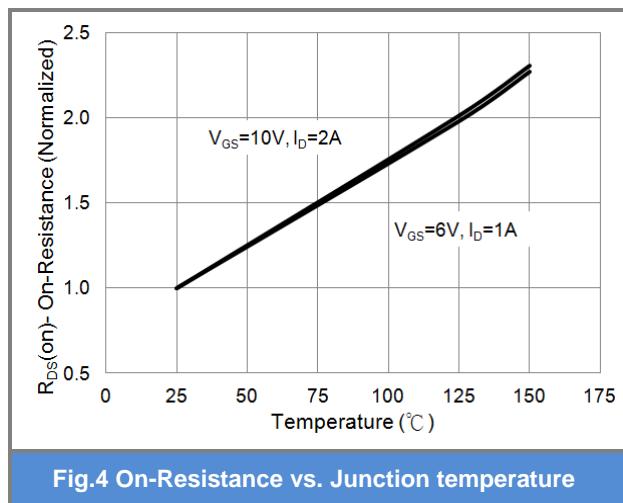


Fig.4 On-Resistance vs. Junction temperature

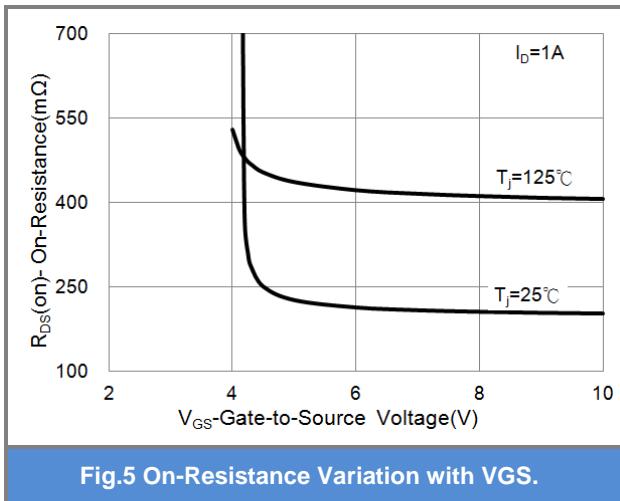


Fig.5 On-Resistance Variation with VGS.

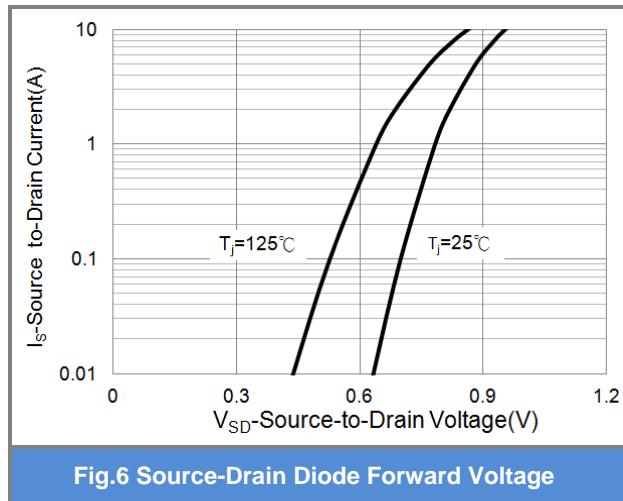


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

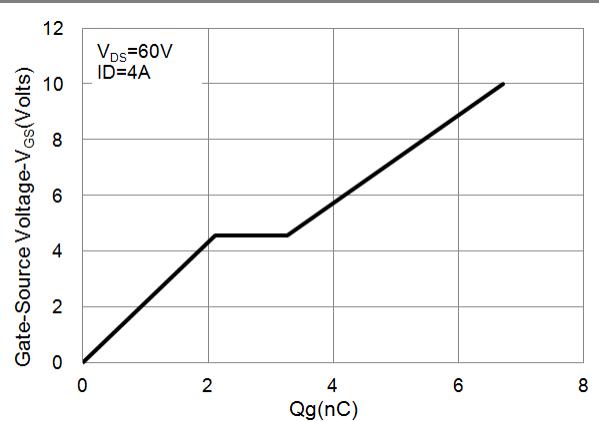


Fig.7 Gate-Charge Characteristics

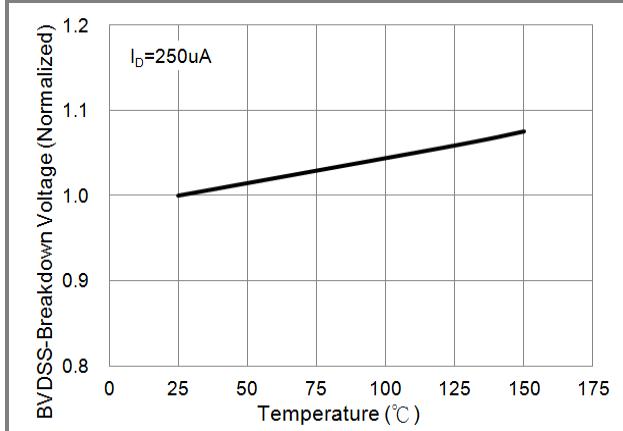


Fig.8 Breakdown Voltage Variation vs. Temperature

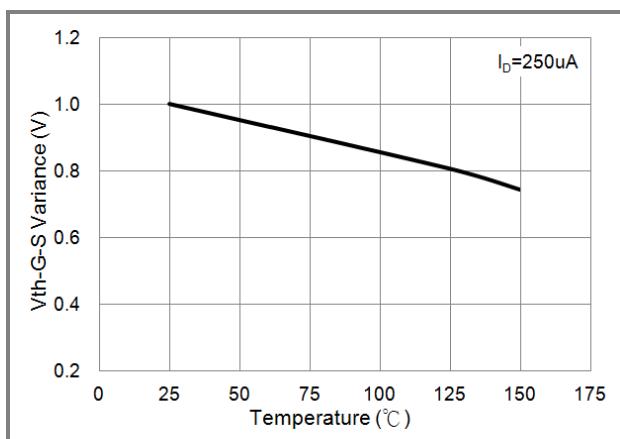


Fig.9 Threshold Voltage Variation with Temperature

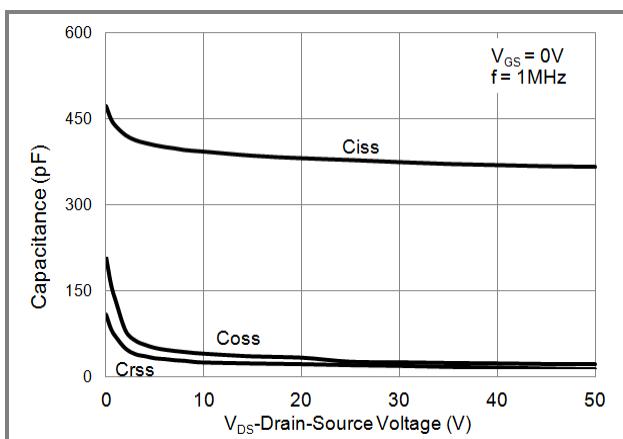


Fig.10 Capacitance vs. Drain-Source Voltage

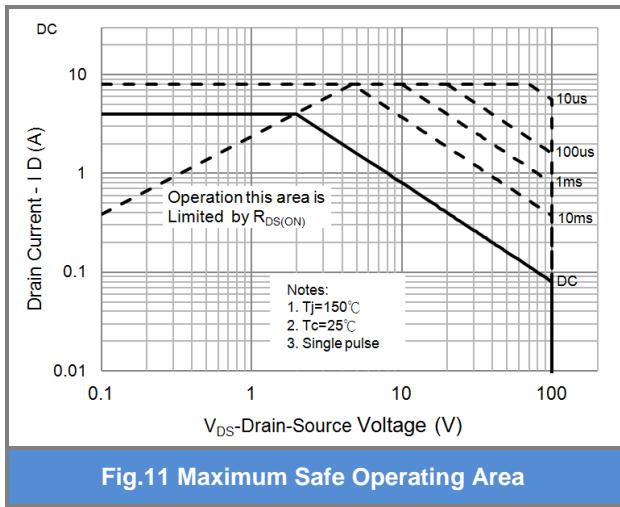


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

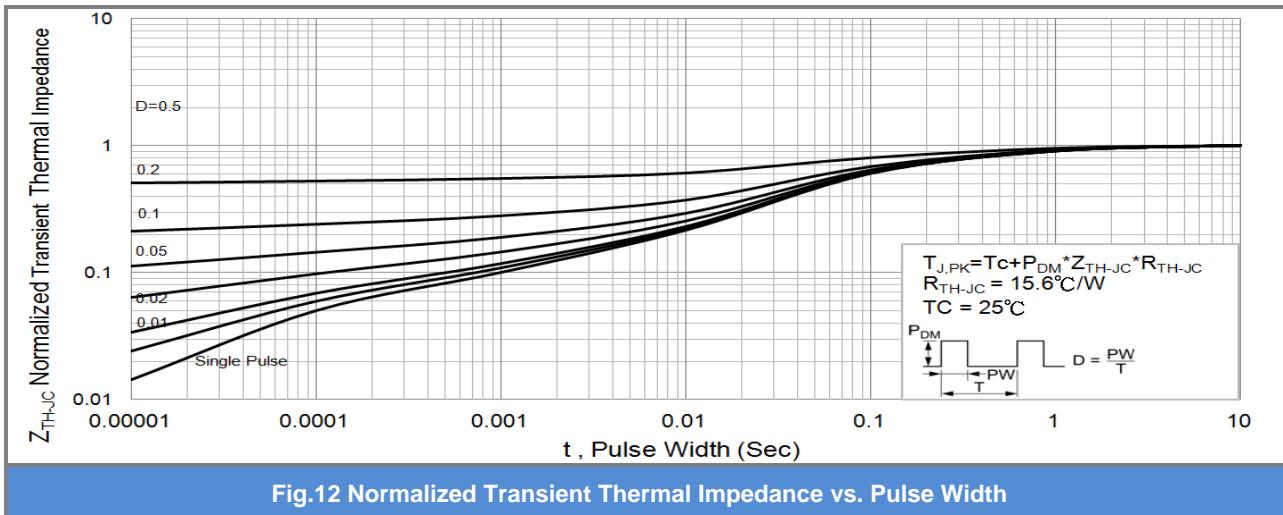
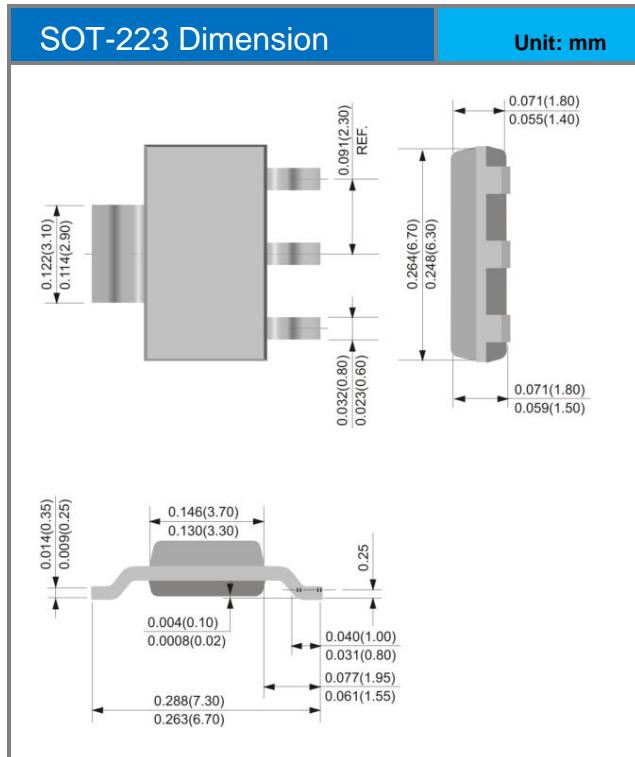


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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Packaging Information



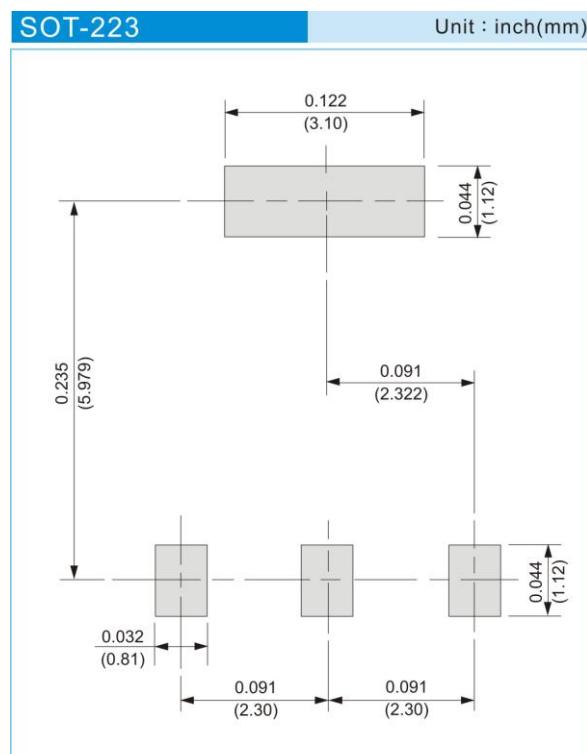


PJW4N10

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJW4N10_R2_00001	SOT-223	2,500pcs / 13" reel	W4N10	Halogen free

MOUNTING PAD LAYOUT





PJW4N10

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